

TITLE

by

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Ph.D. Disseration Prospectus

YEAR

Advisor

ABSTRACT

TITLE HERE

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Abstract here

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Chapter 1

Introduction

1.1 The Conception of Semiconductors

Here we present work by [2, 1].

| Semiconductor | Band Gap (eV) | Electron Mobility ¹ (cm ² /V · s) | Hole Mobility ¹ (cm ² /V · s) | Lattice Constant (Å) |
|---------------|------------------|--|--|-------------------------|
| Si | 1.12 | 1,500 | 470 | 5.43095 ^a |
| Ge | 0.67 | 3,900 | 1,900 | 5.64613 ^a |
| GaAs | 1.42 | 8,500 | 400 | 5.6533 ^b |
| CdS | 2.5 | 300 | 50 | 5.8320 ^c |
| AlAs | 2.16 | 1,200 | 400 | 5.6622 ^b |
| ZnS | 3.66 | 165 | 5 | 5.410 ^d |

Table 1.1: Selected properties of some common semiconductors at $T = 300$ K. Adapted from ref. [5].

¹ Drift mobilities in the purest materials.

^a Diamond cubic crystal structure [4].

^b Zinc blende crystal structure [3].

^c Hexagonal and cubic... citation needed.

^d Notes on ZnS structure.

1.2 Evolution of Semiconductors

1.3 Interest and Development of Two-dimensional Materials

1.4 Current State of Two-dimensional Materials

Chapter 2

Chapter 2

2.1 Section Heading

Chapter 3

Chapter 3

3.1 Section Heading

Chapter 4

Conclusion

4.1 Heading

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